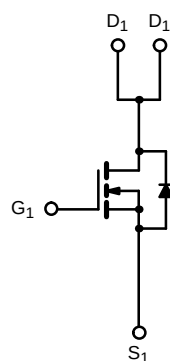
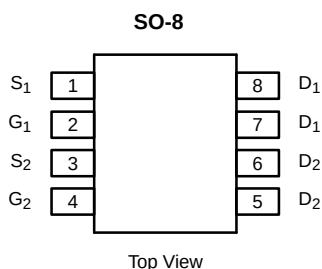




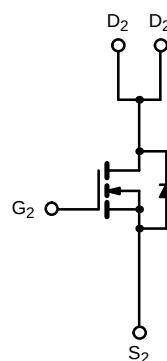
Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.050 @ $V_{GS} = 10$ V	± 5.0
	0.080 @ $V_{GS} = 4.5$ V	± 3.9



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	± 5.0	A
	I_D	± 4.0	
Pulsed Drain Current	I_{DM}	± 40	
Continuous Source Current (Diode Conduction) ^a	I_S	1.7	
Maximum Power Dissipation ^a	P_D	2	W
	P_D	1.3	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	62.5	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

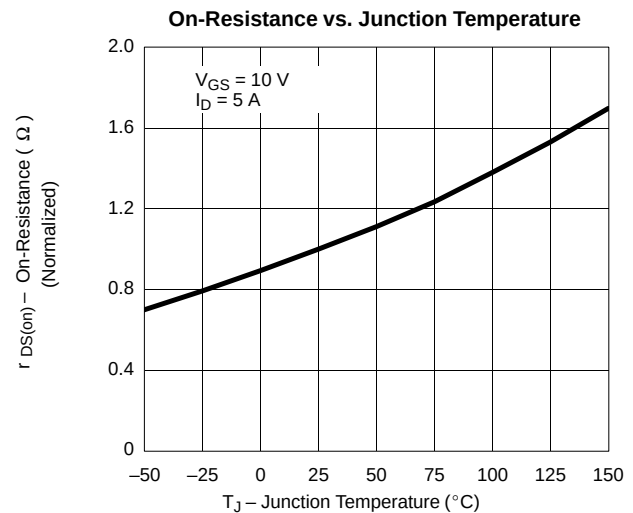
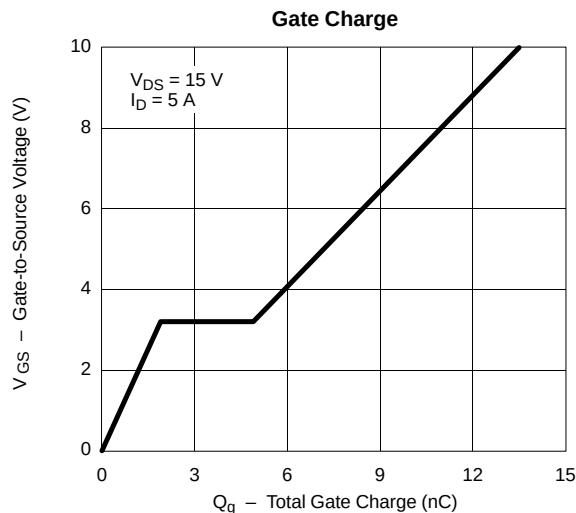
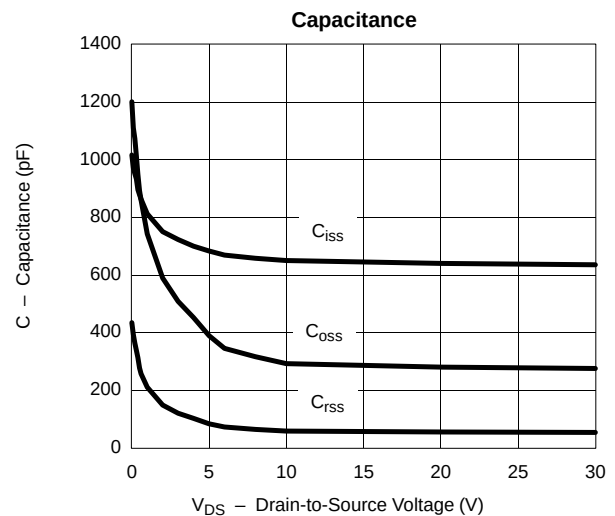
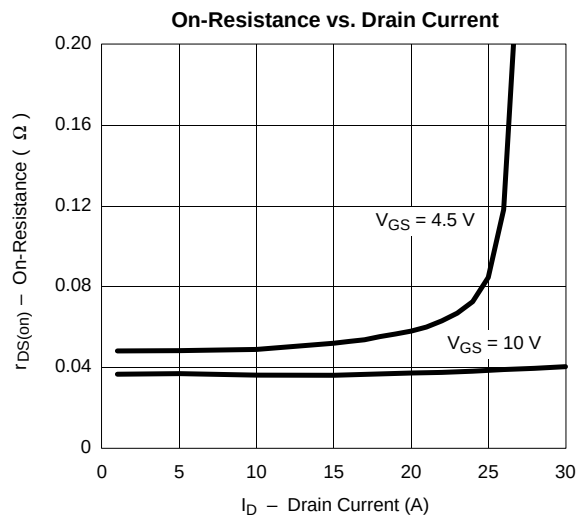
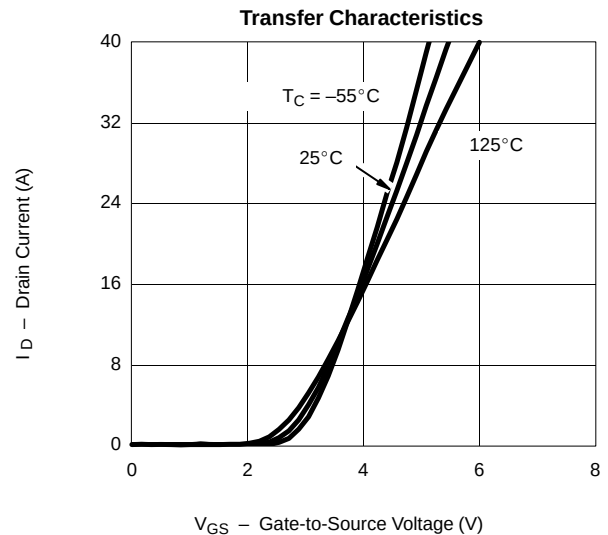
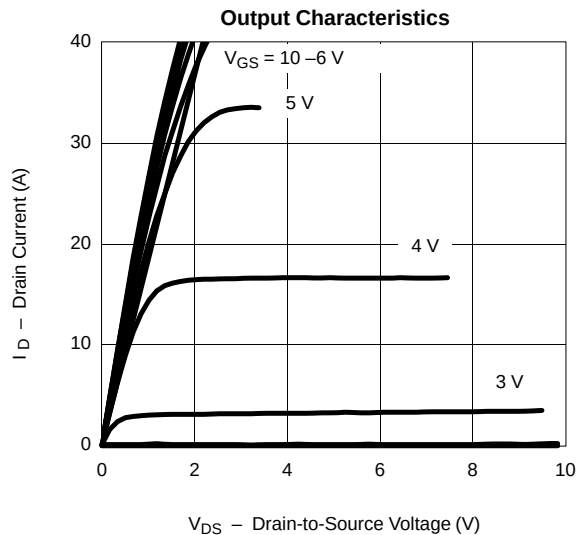
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			2	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55 °C			20	
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	40			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 5.0 A		0.039	0.050	Ω
		V _{GS} = 4.5 V, I _D = 3.9 A		0.052	0.080	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 5.0 A		10		S
Diode Forward Voltage ^b	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.72	1.2	V
Dynamic^a						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 5.0 A		13.5	35	nC
Gate-Source Charge	Q _{gs}			1.9		
Gate-Drain Charge	Q _{gd}			3		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω		11	30	ns
Rise Time	t _r			9	25	
Turn-Off Delay Time	t _{d(off)}			25	50	
Fall Time	t _f			10	50	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 5.0 A, di/dt = 100 A/μs		60	160	

Notes

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

